

512K x 8 LOW VOLTAGE, ULTRA LOW POWER CMOS STATIC RAM

MARCH 2003

FEATURES

- High-speed access time: 55ns, 70ns
- CMOS low power operation
 - 1.5 μ W (typical) CMOS standby
- TTL compatible interface levels
- Single power supply
 - 2.5V--3.6V V_{DD} (62WV5128CLL)
- Fully static operation: no clock or refresh required
- Three state outputs
- Industrial temperature available
- 2 CS Options Available

DESCRIPTION

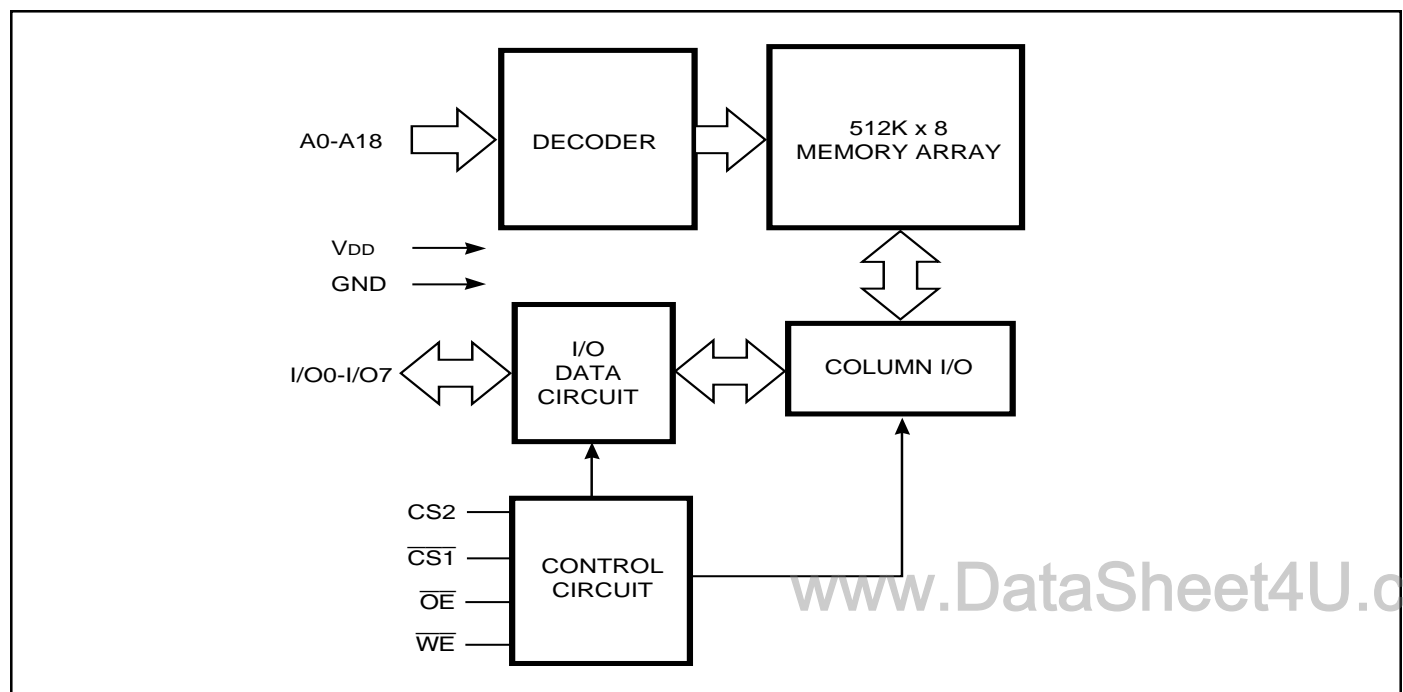
The *ISSI* IS62WV5128CLL are high-speed, 4M bit static RAMs organized as 512K words by 8 bits. It is fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When $\overline{CS1}$ is HIGH (deselected) or when $CS2$ is LOW (deselected) the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable (\overline{WE}) controls both writing and reading of the memory.

The IS62WV5128CLL is packaged in the JEDEC standard 36-pin mini BGA (6mm x 8mm). 36-pin mini BGA is available in both 1CS and 2CS options.

FUNCTIONAL BLOCK DIAGRAM



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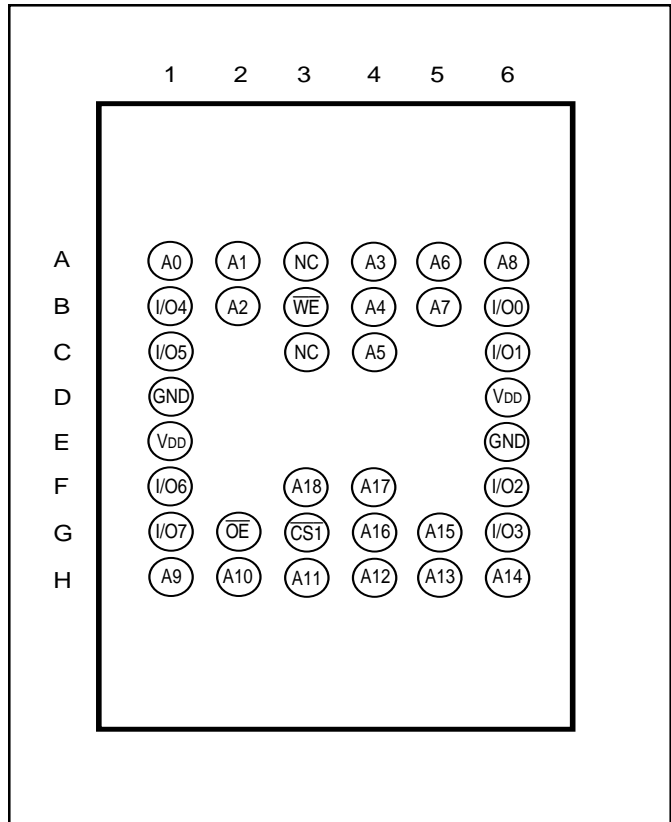
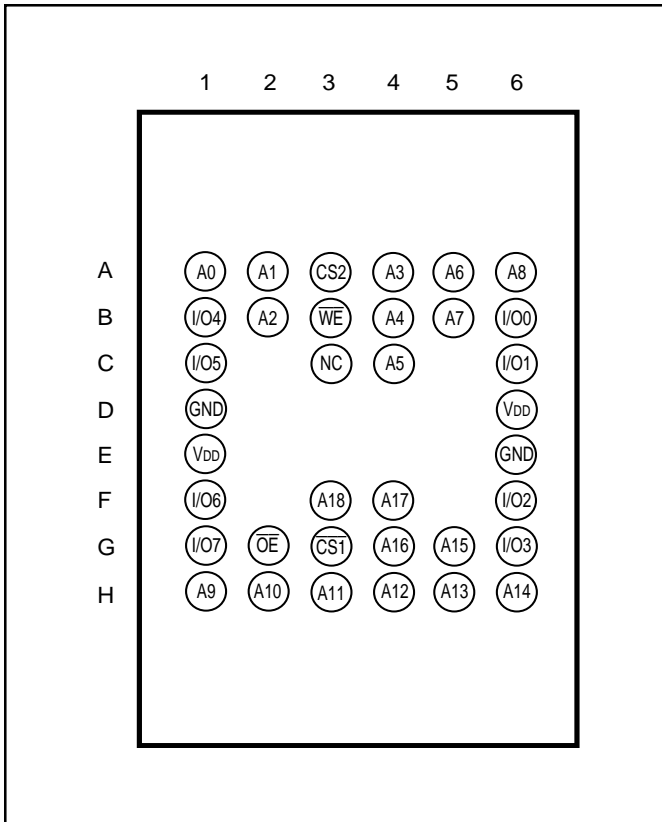
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Rev. 00B
03/13/03

PIN CONFIGURATION

**36-pin mini BGA (B) (6mm x 8mm)
2 CS Option (Package Code B2)**

**36-pin mini BGA (B) (6mm x 8mm)
(Package Code B)**



PIN DESCRIPTIONS

A0-A18	Address Inputs
$\overline{CS1}$	Chip Enable 1 Input
CS2	Chip Enable 2 Input
\overline{OE}	Output Enable Input
\overline{WE}	Write Enable Input
I/O0-I/O7	Input/Output
NC	No Connection
V _{DD}	Power
GND	Ground

OPERATING RANGE (V_{DD})

Range	Ambient Temperature	V_{DD}
Commercial	0°C to +70°C	2.5V - 3.6V
Industrial	-40°C to +85°C	2.5V - 3.6V

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
V_{TERM}	Terminal Voltage with Respect to GND	-0.3 to $V_{DD}+0.5$	V
V_{DD}	V_{DD} Related to GND	-0.2 to +4.2	V
T_{STG}	Storage Temperature	-55 to +125	°C
P_T	Power Dissipation	0.6	W

Note:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	V_{DD}	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	$I_{OH} = -1$ mA	2.5-3.6V	2.2	—	V
V_{OL}	Output LOW Voltage	$I_{OL} = 2.1$ mA	2.5-3.6V	—	0.4	V
V_{IH}	Input HIGH Voltage		2.5-3.6V	2.2	$V_{DD} + 0.3$	V
$V_{IL}^{(1)}$	Input LOW Voltage		2.5-3.6V	-0.2	0.6	V
I_{LI}	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	μ A
I_{LO}	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$, Outputs Disabled		-1	1	μ A

Notes:

1. V_{IL} (min.) = -1.0V for pulse width less than 10 ns.

TRUTH TABLE

Mode	\overline{WE}	$\overline{CS1}$	$CS2$	\overline{OE}	I/O Operation	V_{DD} Current
Not Selected (Power-down)	X	H	X	X	High-Z	I_{SB1} , I_{SB2}
	X	X	L	X	High-Z	I_{SB1} , I_{SB2}
Output Disable	H	L	H	H	High-Z	I_{CC}
Read	H	L	H	L	DOUT	I_{CC}
Write	L	L	H	X	DIN	I_{CC}

CAPACITANCE⁽¹⁾

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	8	pF
C _{OUT}	Input/Output Capacitance	V _{OUT} = 0V	10	pF

Note:

1. Tested initially and after any design or process changes that may affect these parameters.

AC TEST CONDITIONS

Parameter	62WV5128CLL (Unit)
Input Pulse Level	0.4 to V _{DD} -0.3V
Input Rise and Fall Times	5ns
Input and Output Timing and Reference Level	V _{REF}
Output Load	See Figures 1 and 2

2.5V - 3.6V	
R1(Ω)	3070
R2(Ω)	3150
V _{REF}	1.5V
V _{TM}	2.8V

AC TEST LOADS

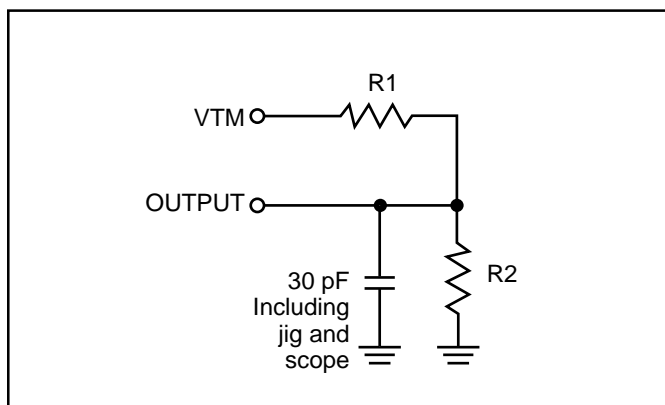


Figure 1

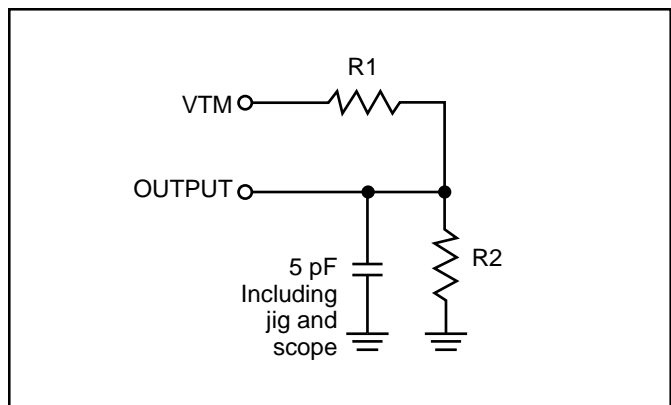


Figure 2

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)**62WV5128CLL** (2.5V - 3.6V)

Symbol	Parameter	Test Conditions		Max.		Unit
				55 ns	70 ns	
I _{CC}	V _{DD} Dynamic Operating Supply Current	V _{DD} =Max.,	Com.	50	45	mA
		I _{OUT} =0 mA, f=f _{MAX}	Ind.	55	50	
I _{CC1}	Operating Supply Current	V _{DD} =Max.,	Com.	2	2	mA
		I _{OUT} =0 mA, f=0	Ind.	3	3	
I _{SB1}	TTL Standby Current (TTL Inputs)	V _{DD} =Max.,	Com.	0.6	0.6	mA
		V _{IN} =V _{IH} or V _{IL} , CS1=V _{IH} , CS2=V _{IL} , f=1 MHz	Ind.	0.8	0.8	
I _{SB2}	CMOS Standby Current (CMOS Inputs)	V _{DD} =Max.,	Com.	10	10	μA
		CS1 ≥ V _{DD} -0.2V,	Ind.	10	10	
		CS2 ≤ 0.2V,	typ ⁽²⁾	0.5	0.5	
		V _{IN} ≥ V _{DD} -0.2V, or V _{IN} ≤ 0.2V, f = 0				

Note:

- At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- Typical values are measured at V_{DD} = 3.0V, T_A = 25°C. Not 100% tested.

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

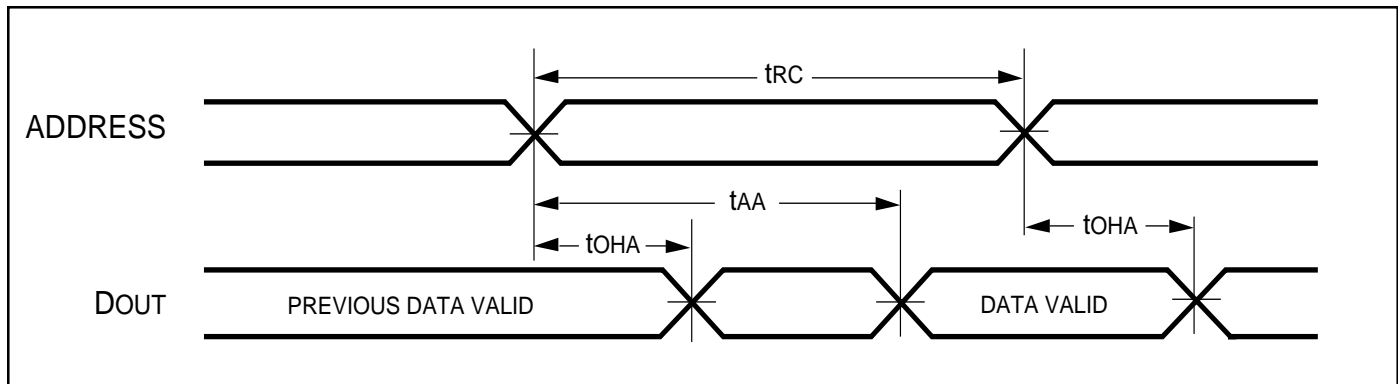
Symbol	Parameter	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t _{RC}	Read Cycle Time	55	—	70	—	ns
t _{AA}	Address Access Time	—	55	—	70	ns
t _{OHA}	Output Hold Time	10	—	10	—	ns
t _{ACS1} /t _{ACS2}	CS1/CS2 Access Time	—	55	—	70	ns
t _{DOE}	OE Access Time	—	35	—	40	ns
t _{HZOE} ⁽²⁾	OE to High-Z Output	—	20	—	25	ns
t _{LZOE} ⁽²⁾	OE to Low-Z Output	5	—	5	—	ns
t _{HZCS1} /t _{HZCS2} ⁽²⁾	CS1/CS2 to High-Z Output	0	20	0	25	ns
t _{LZCS1} /t _{LZCS2} ⁽²⁾	CS1/CS2 to Low-Z Output	10	—	10	—	ns

Notes:

- Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0.4 to V_{DD}-0.3V and output loading specified in Figure 1.
- Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

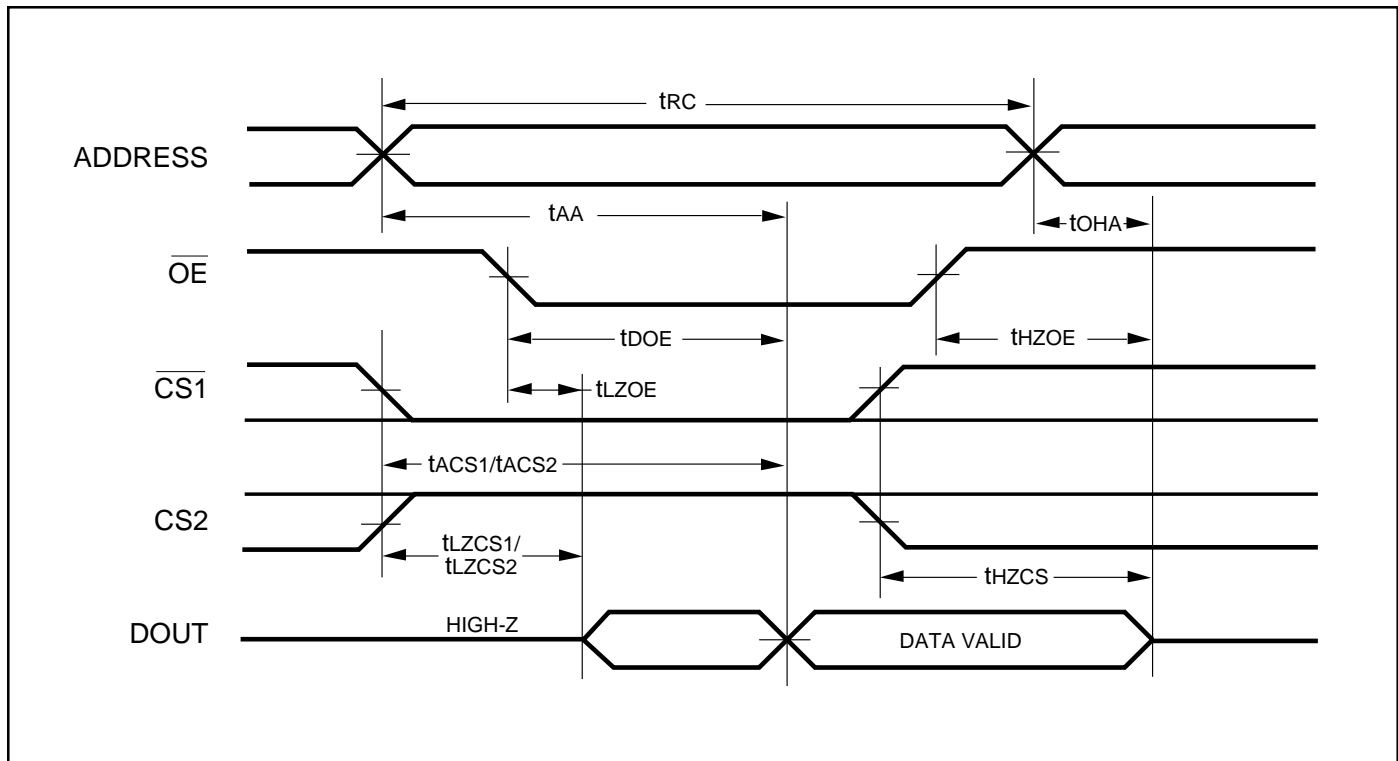
AC WAVEFORMS

READ CYCLE NO. 1^(1,2) (Address Controlled) ($\overline{CS1} = \overline{OE} = V_{IL}$, $CS2 = \overline{WE} = V_{IH}$)



AC WAVEFORMS

READ CYCLE NO. 2^(1,3) ($\overline{CS1}$, $CS2$, \overline{OE} Controlled)



Notes:

1. \overline{WE} is HIGH for a Read Cycle.
2. The device is continuously selected. \overline{OE} , $\overline{CS1} = V_{IL}$. $CS2 = \overline{WE} = V_{IH}$.
3. Address is valid prior to or coincident with $\overline{CS1}$ LOW and $CS2$ HIGH transition.

WRITE CYCLE SWITCHING CHARACTERISTICS^(1,2) (Over Operating Range)

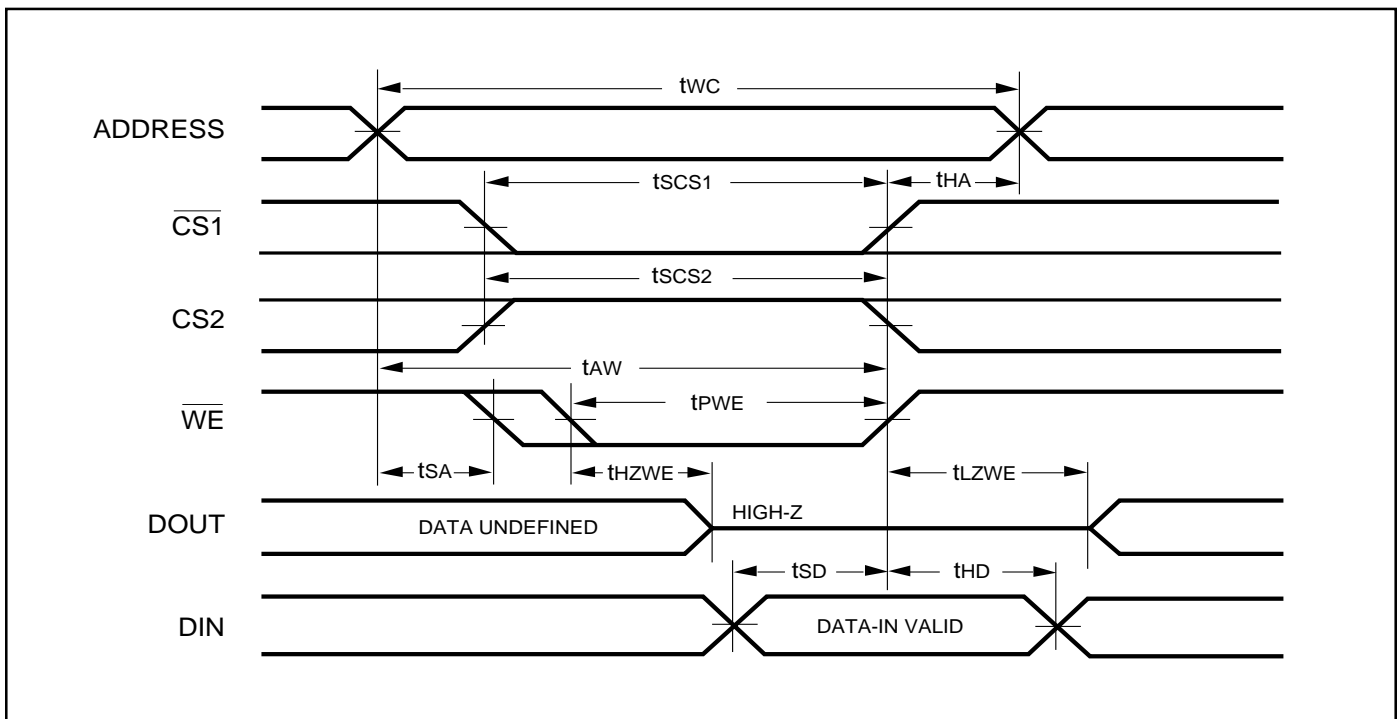
Symbol	Parameter	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t _{WC}	Write Cycle Time	55	—	70	—	ns
t _{SCS1} /t _{SCS2}	$\overline{CS1}/CS2$ to Write End	45	—	60	—	ns
t _{AW}	Address Setup Time to Write End	45	—	60	—	ns
t _{HA}	Address Hold from Write End	0	—	0	—	ns
t _{SA}	Address Setup Time	0	—	0	—	ns
t _{PWE}	\overline{WE} Pulse Width	40	—	50	—	ns
t _{SD}	Data Setup to Write End	25	—	30	—	ns
t _{HD}	Data Hold from Write End	0	—	0	—	ns
t _{HZWE⁽³⁾}	\overline{WE} LOW to High-Z Output	—	20	—	20	ns
t _{LZWE⁽³⁾}	\overline{WE} HIGH to Low-Z Output	5	—	5	—	ns

Notes:

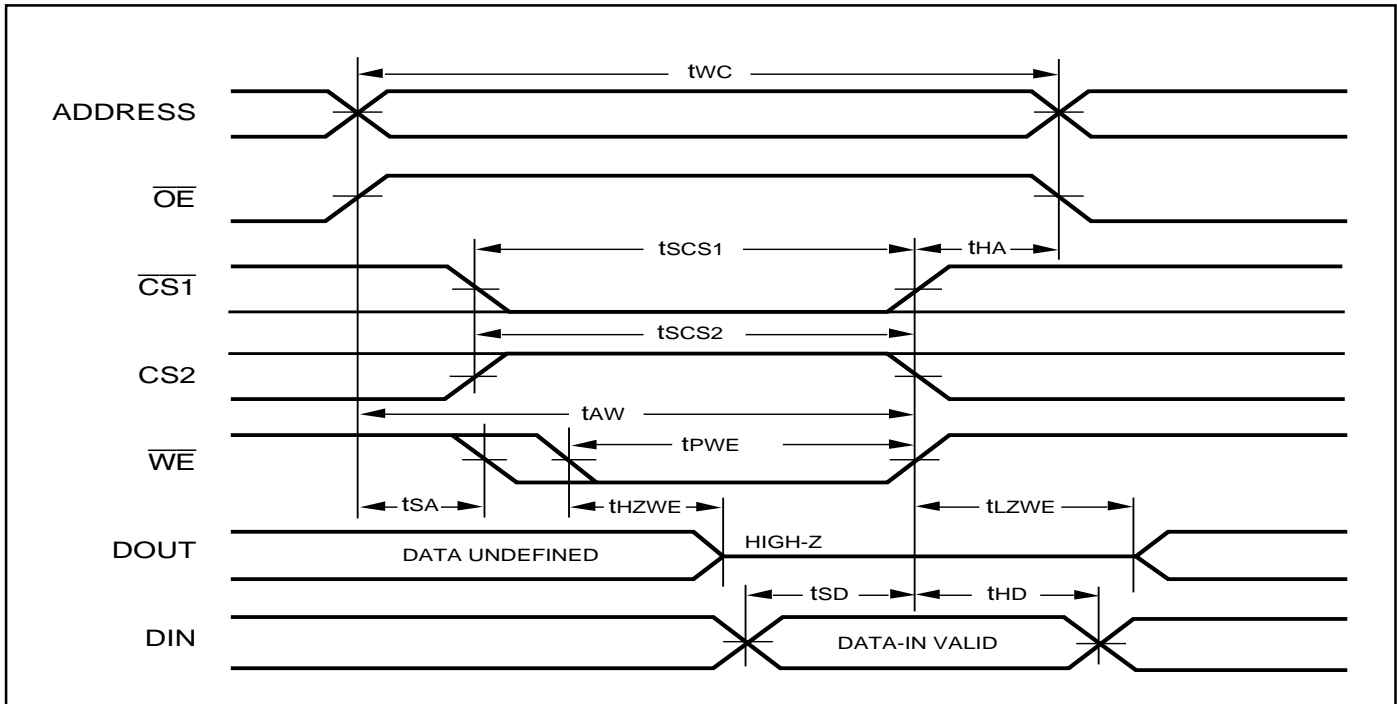
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0.4V to V_{DD}-0.3V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of $\overline{CS1}$ LOW, CS2 HIGH and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

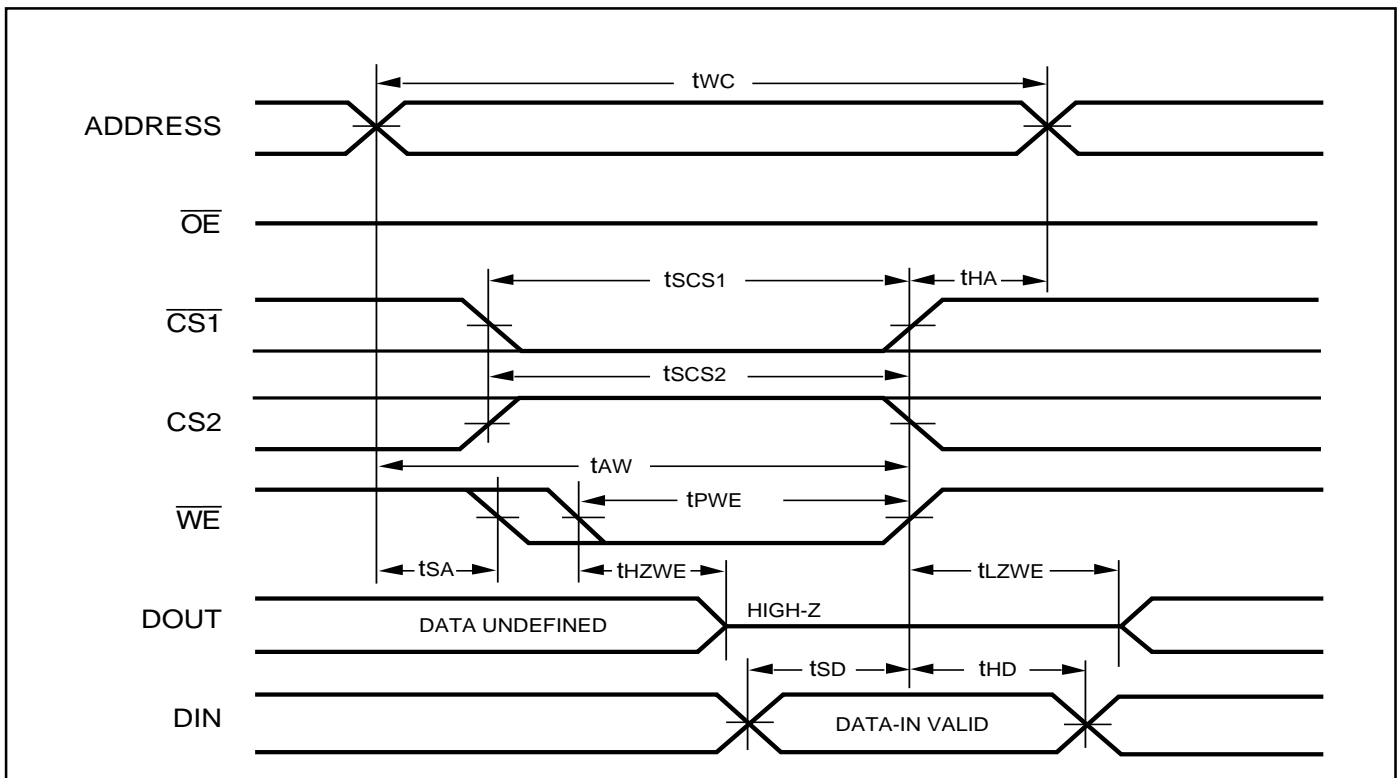
WRITE CYCLE NO. 1 ($\overline{CS1}/CS2$ Controlled, \overline{OE} = HIGH or LOW)



WRITE CYCLE NO. 2 (\overline{WE} Controlled: \overline{OE} is HIGH During Write Cycle)

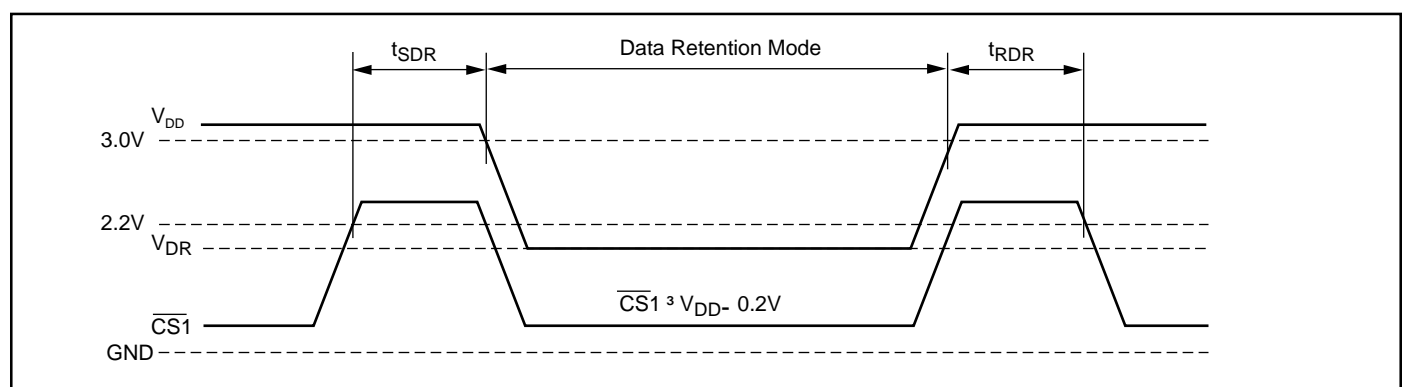


WRITE CYCLE NO. 3 (\overline{WE} Controlled: \overline{OE} is LOW During Write Cycle)

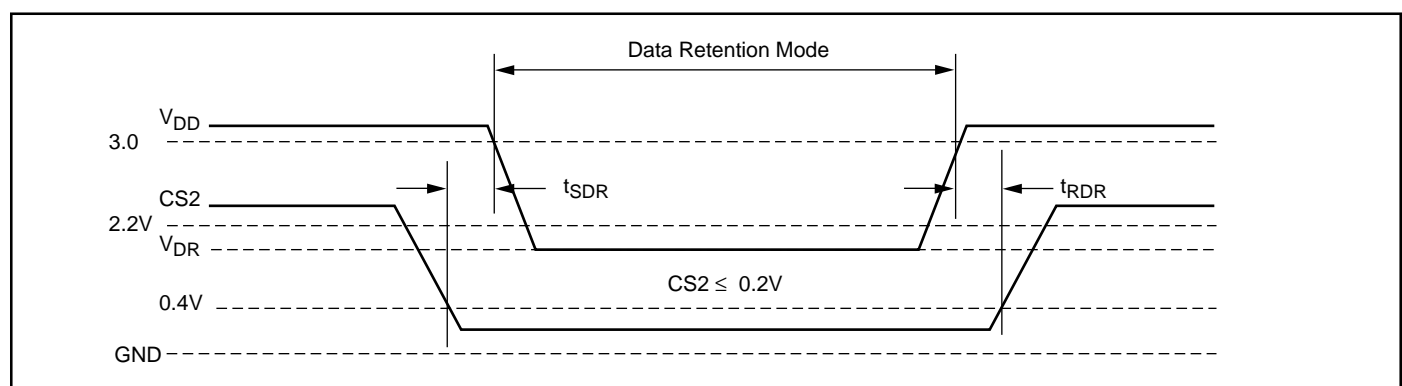


DATA RETENTION SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition	Min.	Max.	Unit
V _{DR}	V _{DD} for Data Retention	See Data Retention Waveform	1.5	3.6	V
I _{DR}	Data Retention Current	V _{DD} = 1.5V, $\overline{CS1}/CS2 \geq V_{DD} - 0.2V$	—	10	μA
t _{SDR}	Data Retention Setup Time	See Data Retention Waveform	0	—	ns
t _{RDR}	Recovery Time	See Data Retention Waveform	t _{RC}	—	ns

DATA RETENTION WAVEFORM ($\overline{CS1}$ Controlled)

DATA RETENTION WAVEFORM (CS2 Controlled)



ORDERING INFORMATION**IS62WV5128CLL (2.5V - 3.6V)****Commercial Range: 0°C to +70°C**

Speed (ns)	Order Part No.	Package
55	IS62WV5128CLL-55B	mini BGA (6mm x 8mm)
55	IS62WV5128CLL-55B2	mini BGA (6mm x 8mm) 2CS

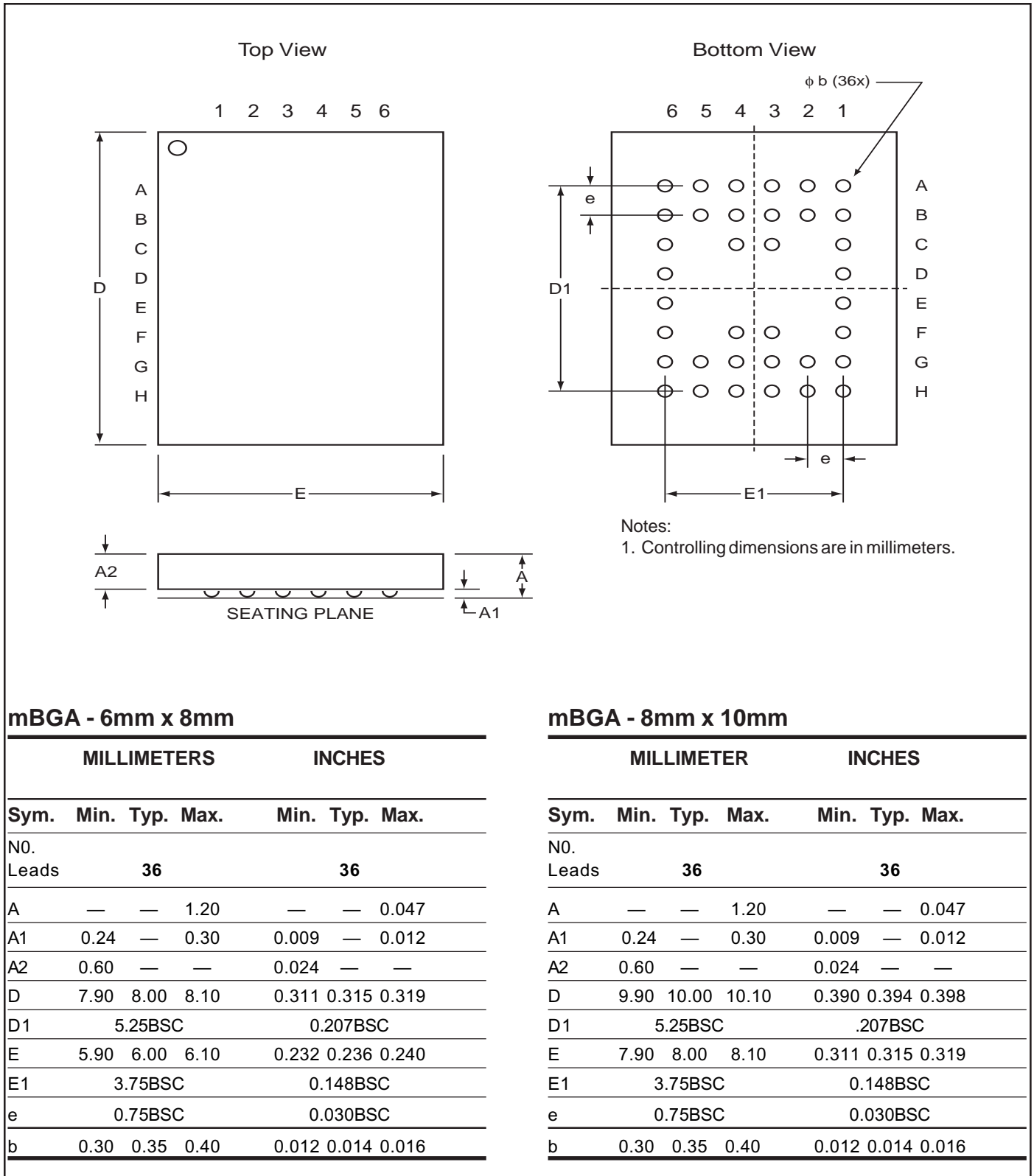
Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS62WV5128CLL-55BI	mini BGA (6mm x 8mm)
55	IS62WV5128CLL-55B2I	mini BGA (6mm x 8mm) 2CS
70	IS62WV5128CLL-70BI	mini BGA (6mm x 8mm)
70	IS62WV5128CLL-70B2I	mini BGA (6mm x 8mm) 2CS

PACKAGING INFORMATION



Mini Ball Grid Array Package Code: B (36-pin)



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Rev. E
01/15/03